



# UVA

SCHOOL *of* ENGINEERING  
& APPLIED SCIENCE

## Thermal transport in UWBG materials and interfaces: Challenges in measurements and understanding

**Patrick E. Hopkins**

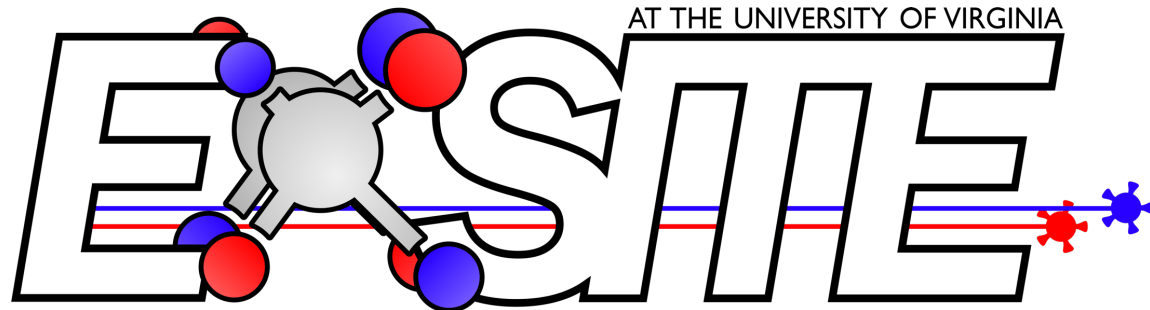
Professor

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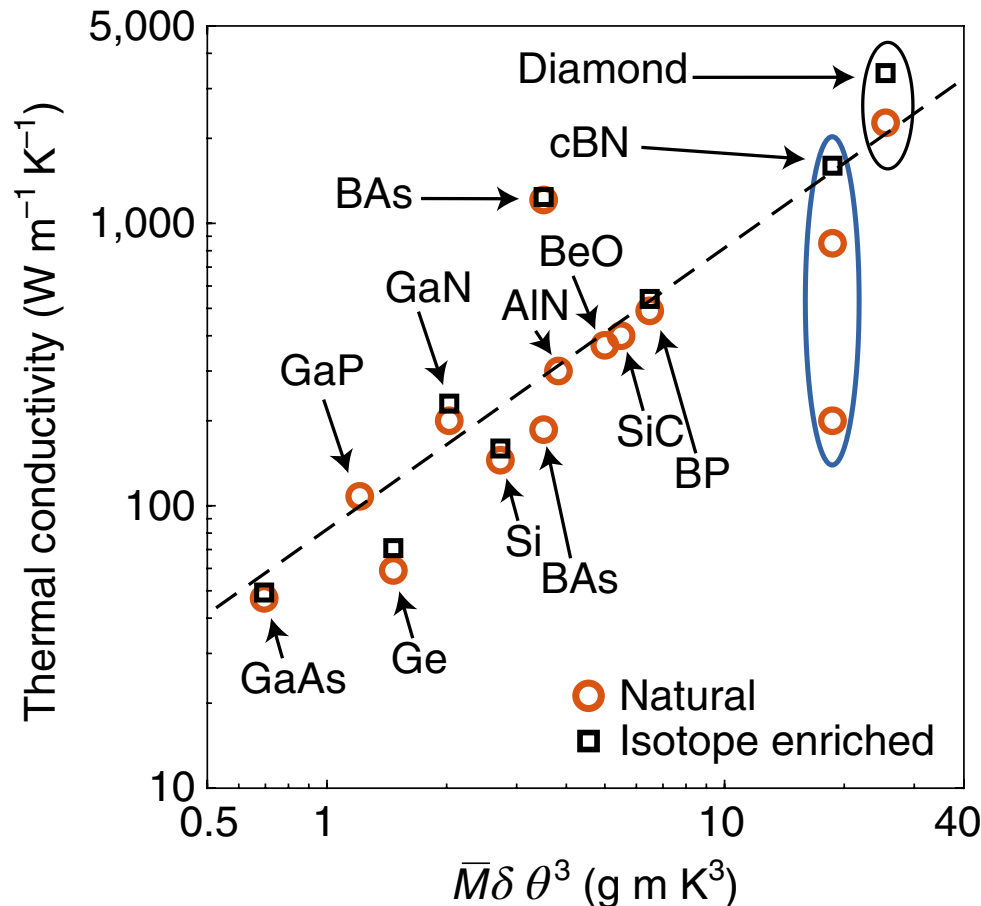
[patrickehopkins.com](http://patrickehopkins.com)



# Nanoscopic picture of the thermal conductivity of materials

## Thermal conductivity of materials

How do you make a great thermal conductor?



$$\kappa = \frac{1}{3} C v \lambda = \frac{1}{3} C v_g^2 \tau$$

### High $\kappa$

- Stiff, light mass, small unit cell, no defects,

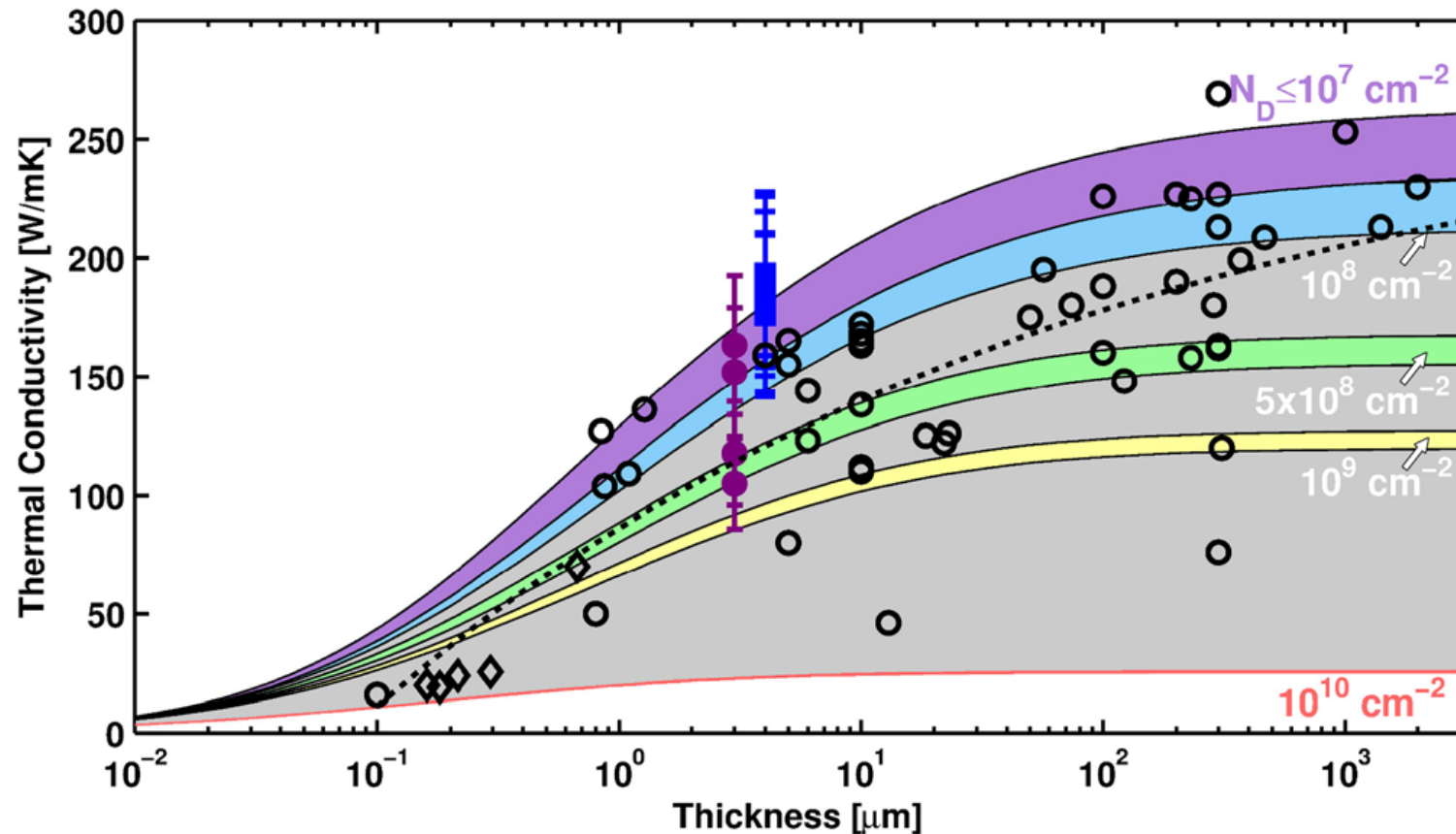
### Low $\kappa$

- Soft, heavy mass, large unit cell, complex unit cell, mass/chemical heterogeneities

## Nanoscale heat transfer of materials

But defects and interfaces impact  $\kappa$

Ex: the case of GaN thin films



# The ONR MURI Team (PMs: Lynn Petersen & Mark Spector)



UNIVERSITY OF  
MARYLAND

**Sam Graham**



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**Asif Kahn**



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**Karl Hobart**

**Marko Tadjer**

**Travis Anderson**

**Georgia  
Tech**



**W. Alan Doolittle**



**Asegun Henry**

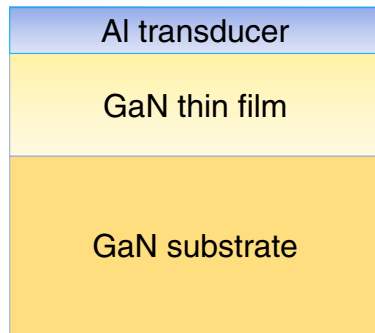


# The importance of low defects films

Homoepitaxially grown GaN films exhibit exceptionally larger thermal conductivities

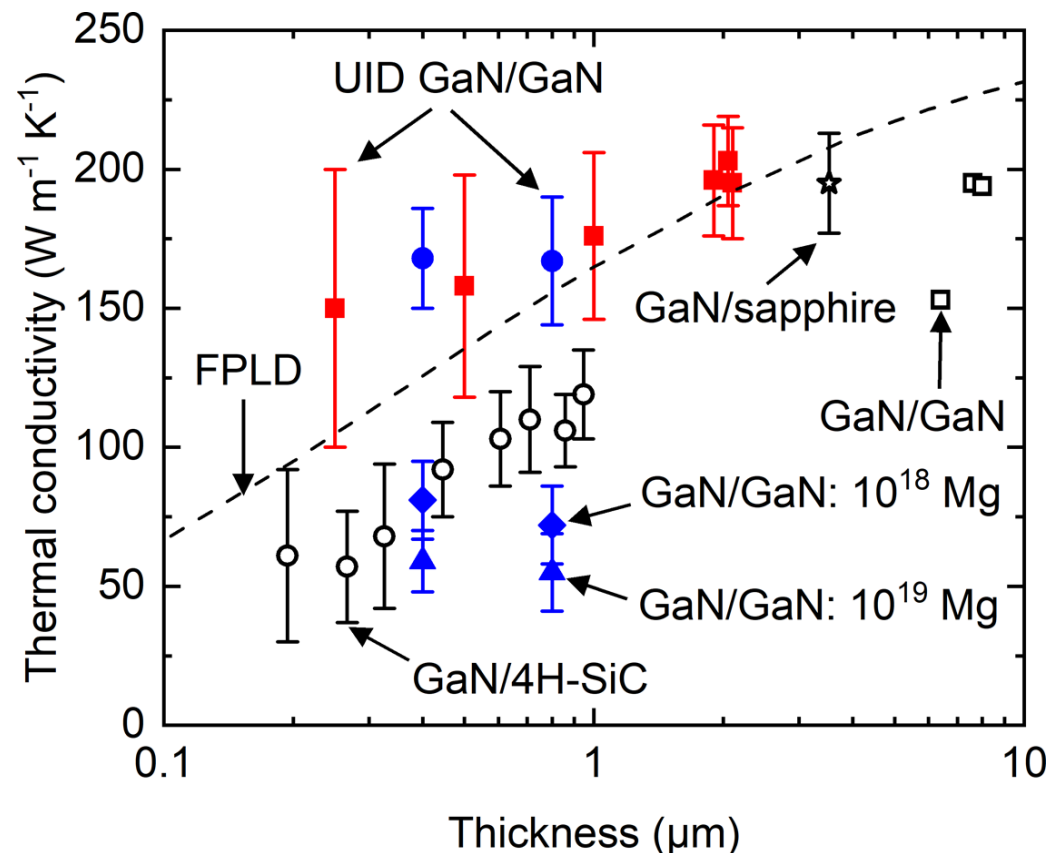
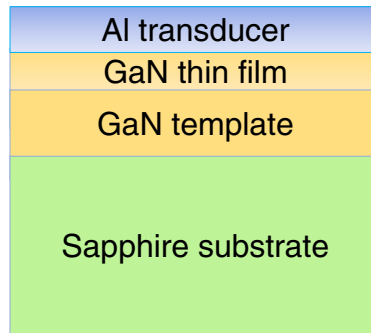
Hite  
NRL

(a) MOCVD-grown



Doolittle  
Ga Tech

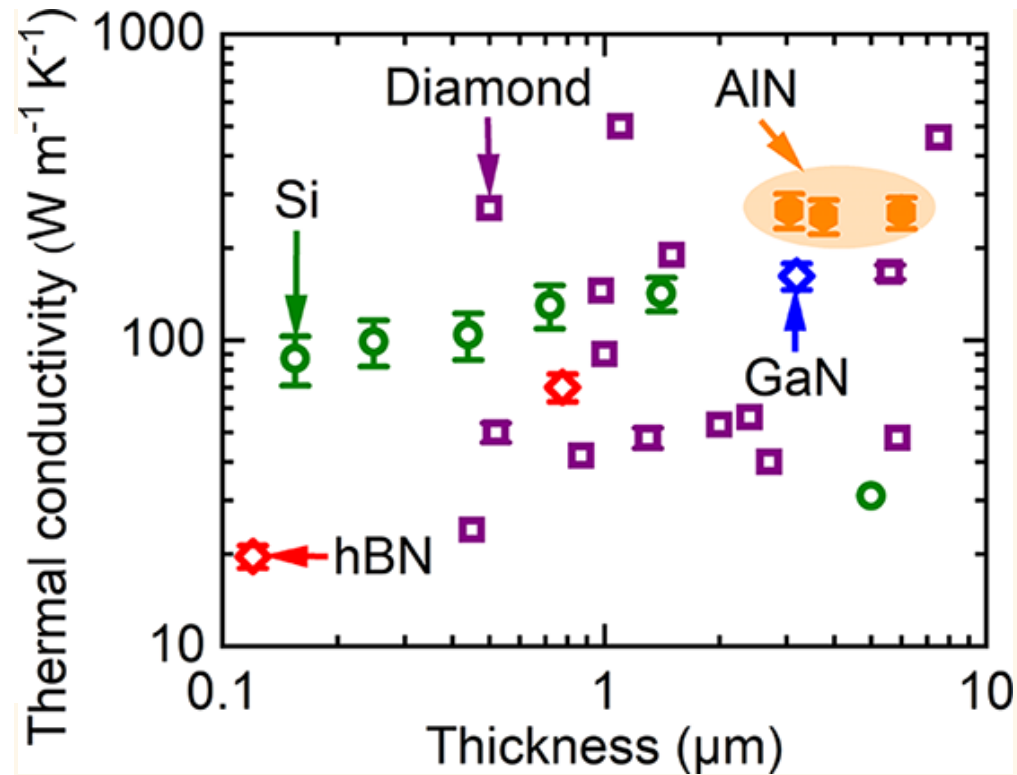
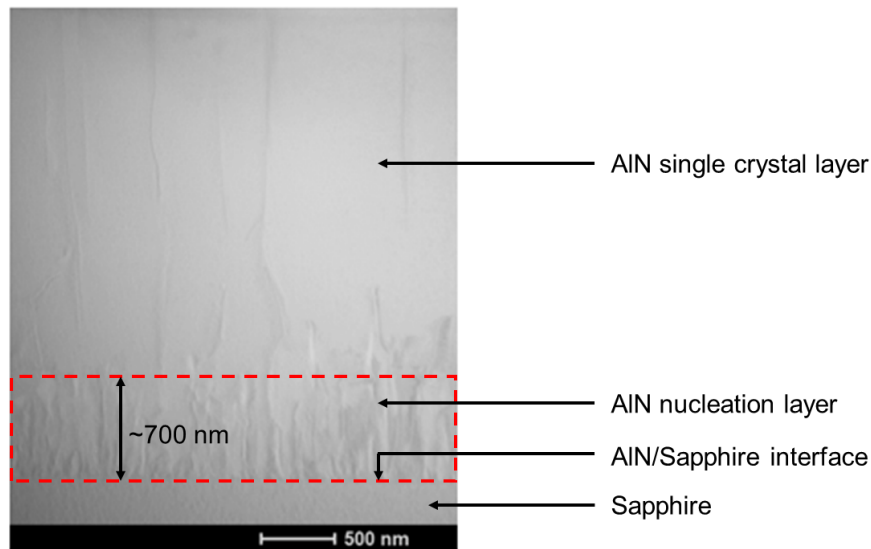
(b) MBE-grown



# The importance of low defects films

Exceptionally high *in plane* thermal conductivity of AlN films grown on sapphire substrates

Kahn  
U. South Carolina



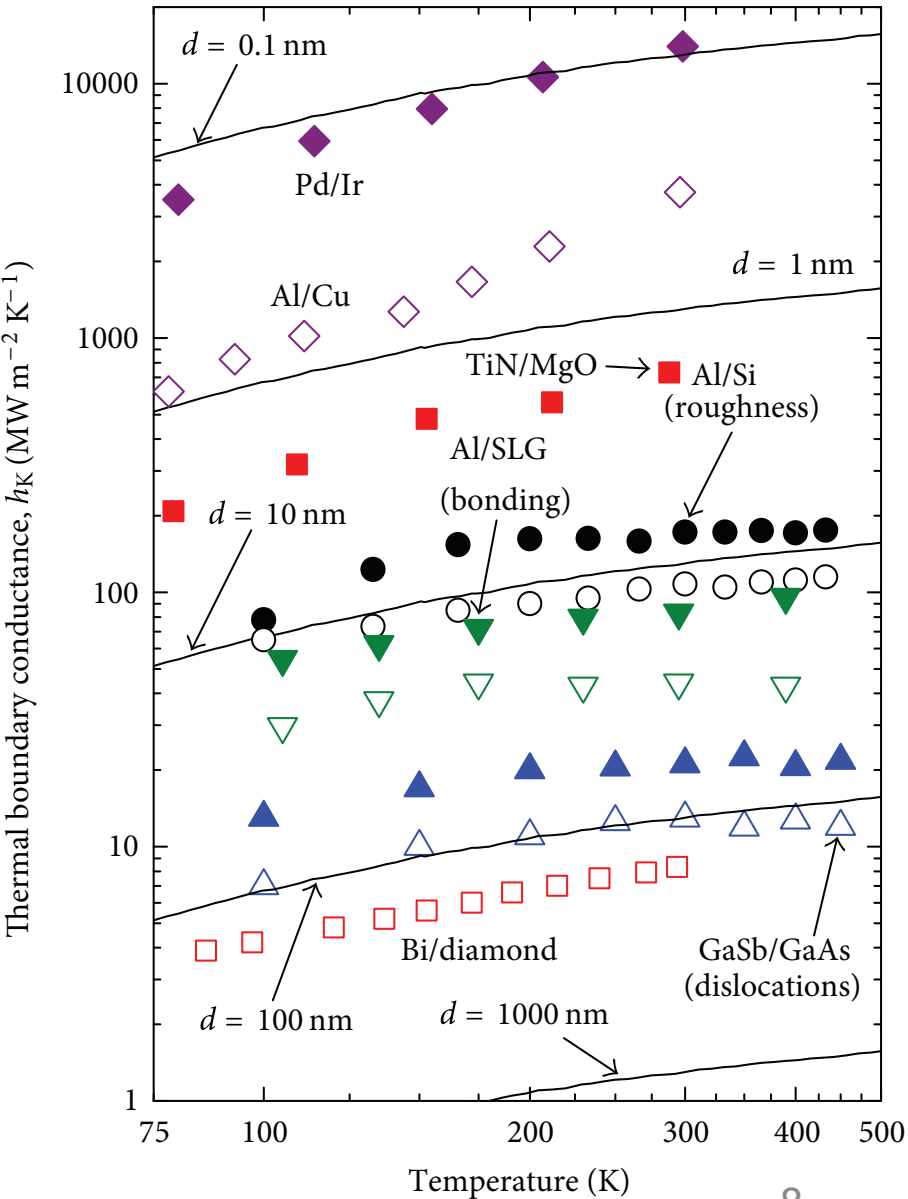
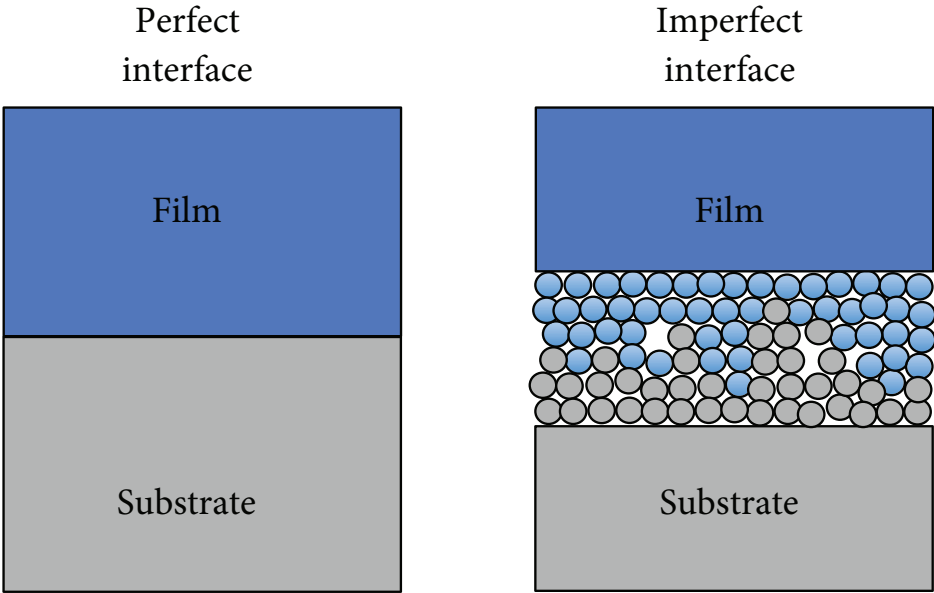
# Goals for talk today: Major technical challenges in measurement and understanding of electron and phonon transport across WBG and UWBG interfaces

- **Technical challenge – Interfaces:** Designing interfaces to reduce TBR
  - Can we move beyond intrinsic phonon limitations in materials?  
*The “interfacial modes” and the “superlattice modes”*
  - Can we create new pathways for heat flow? *Electron “thermal short circuits” and thermal diodes*
- **Technical challenge – Measurements:** Thermal conductivity and TBR measurements at device relevant length scales
  - Thermoreflectance-based techniques offer current state of the art
  - Limitations for measuring certain device-scale resistances
  - Need for turn-key thermal conductivity measurement tool for thin films that does not require expert in thermoreflectance

# Major technical challenge: thermal boundary resistance

$$q = h_K \Delta T = \frac{1}{R_K} \Delta T$$

Interfacial quality and chemistry matters

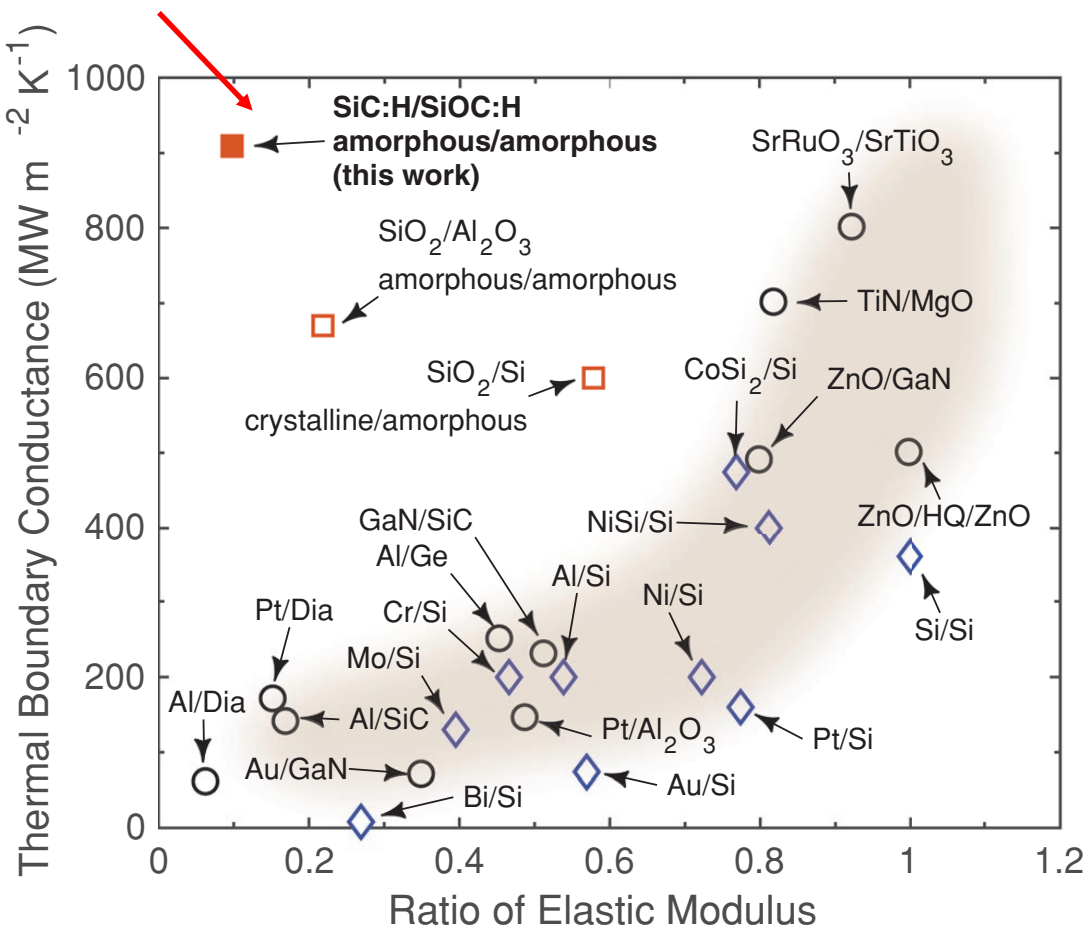
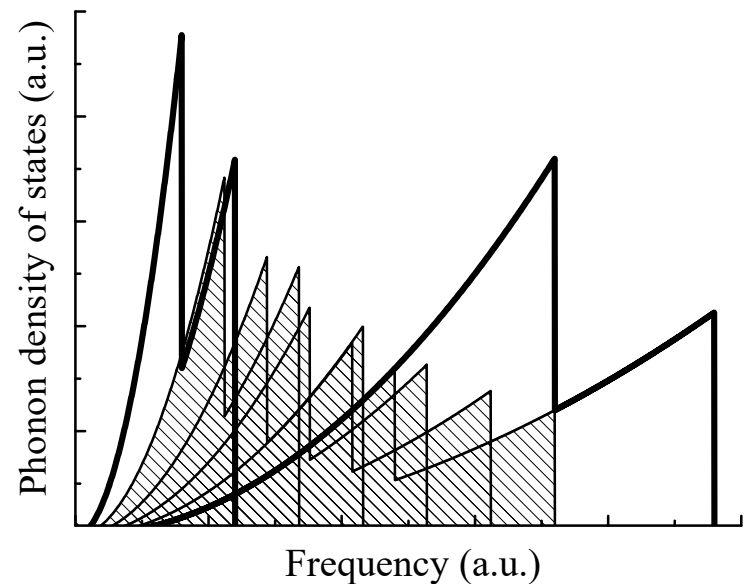


ISRN Mech. Eng. **2013**, 682586  
Adv. Func. Mat. **30**, 1903857  
Ann. Rev. Mat. Sci. **46**, 433

# Intrinsic limitations from the “phonon mismatch” picture

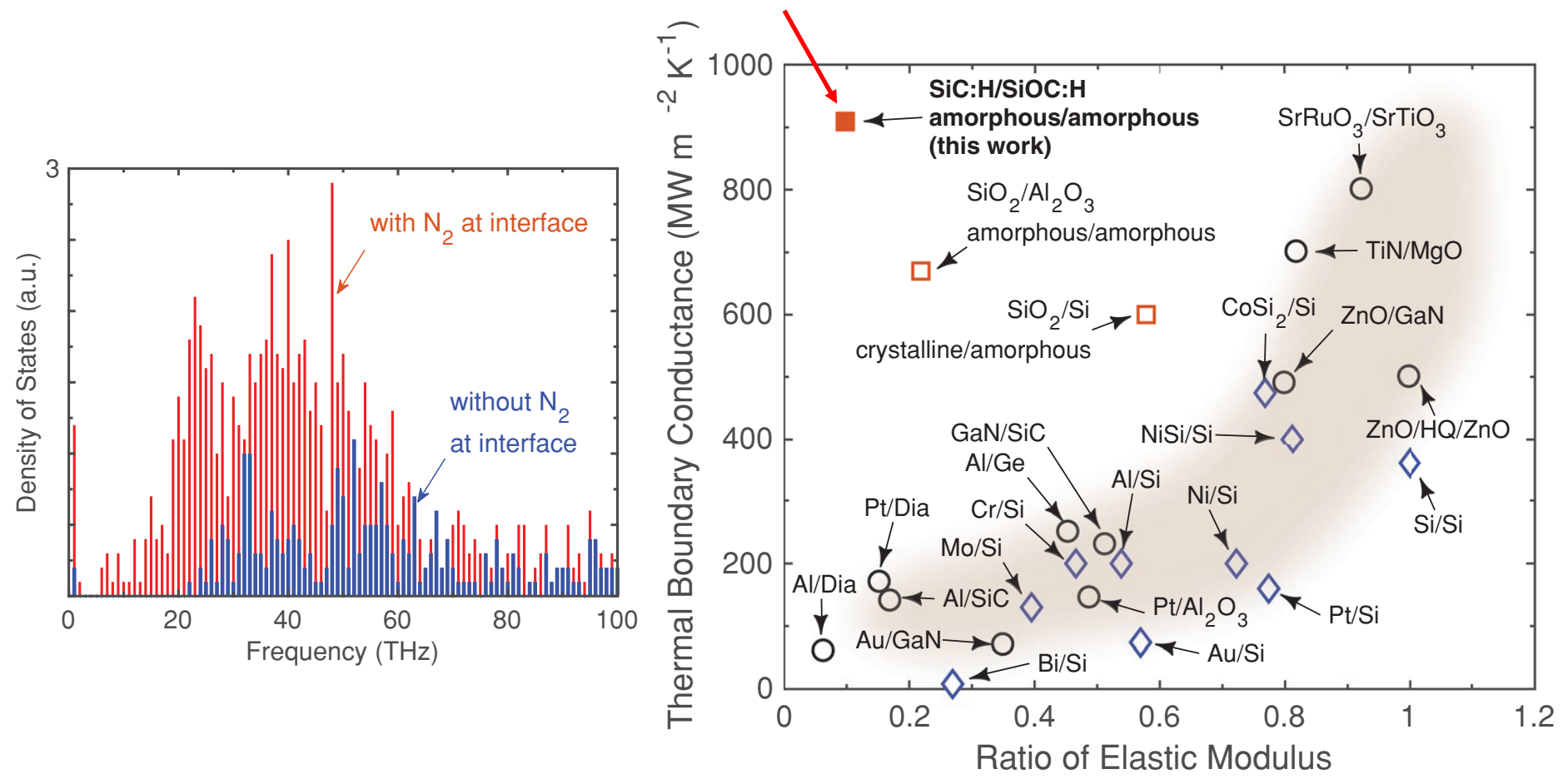
Why aren't these materials restricted by same phononic mismatch trends?

Phonon density of states mismatch can intrinsically limit TBC



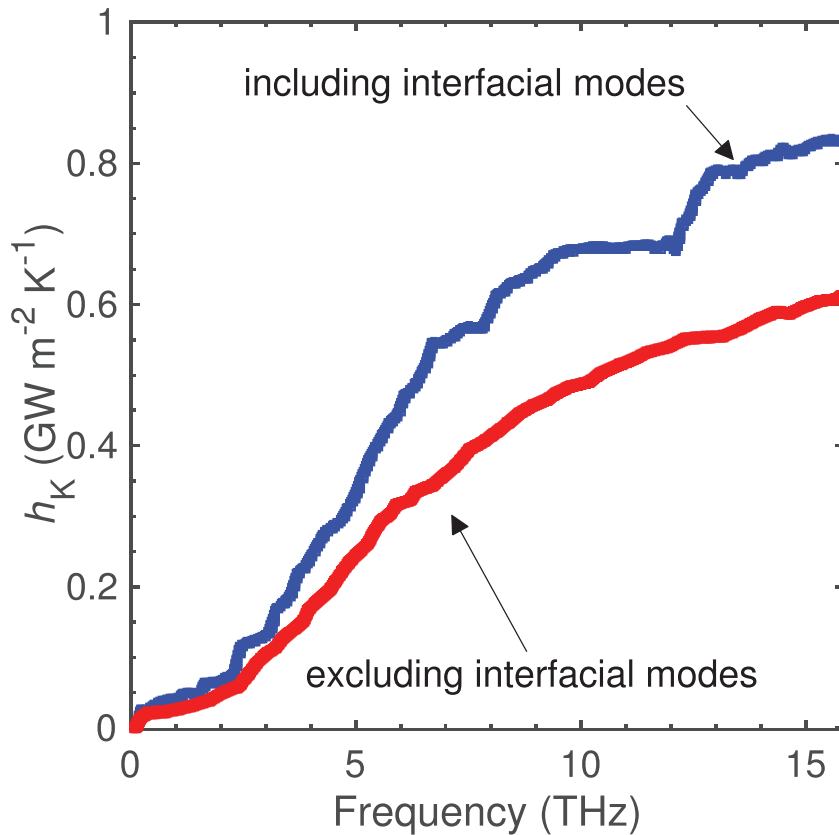
# Intrinsic limitations from the “phonon mismatch” picture

Interfacial defects can enhance thermal transport across interfaces

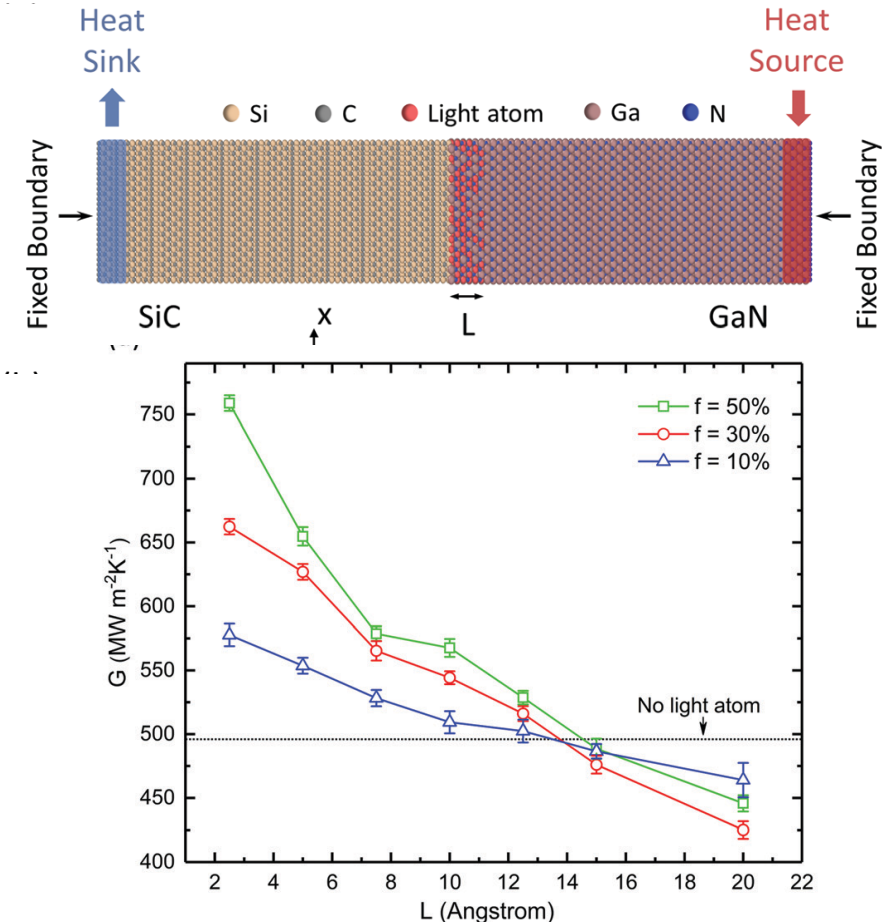


# Interfacial modes can enhance TBC/reduce TBR

And interfacial defects can control the population and density of states of these modes



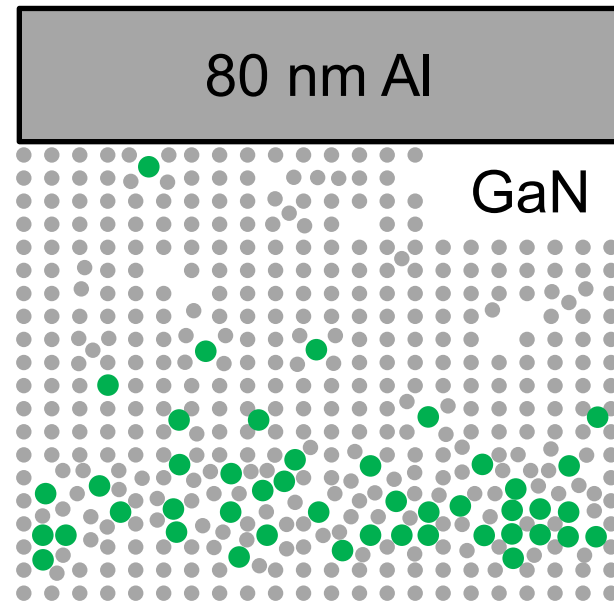
Gordiz and Henry,  
*J. Appl. Phys.* **119**, 015101



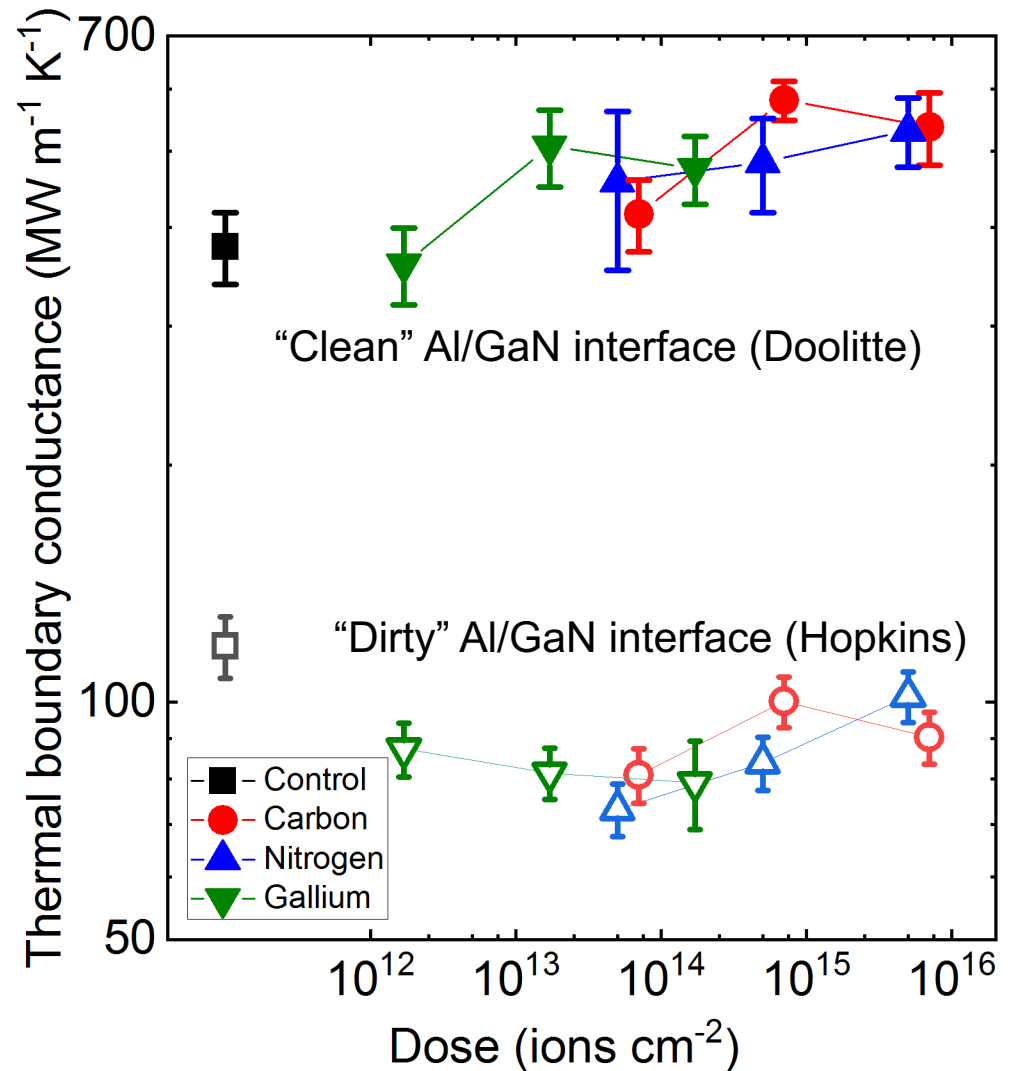
Lee and Luo, *Appl. Phys. Lett.*  
**112**, 011603

# Ion-irradiation induced defects enhance GaN phonon TBC

And interfacial defects can control the population and density of states of these modes



400 keV He<sup>+</sup> implants:  
end of range dep

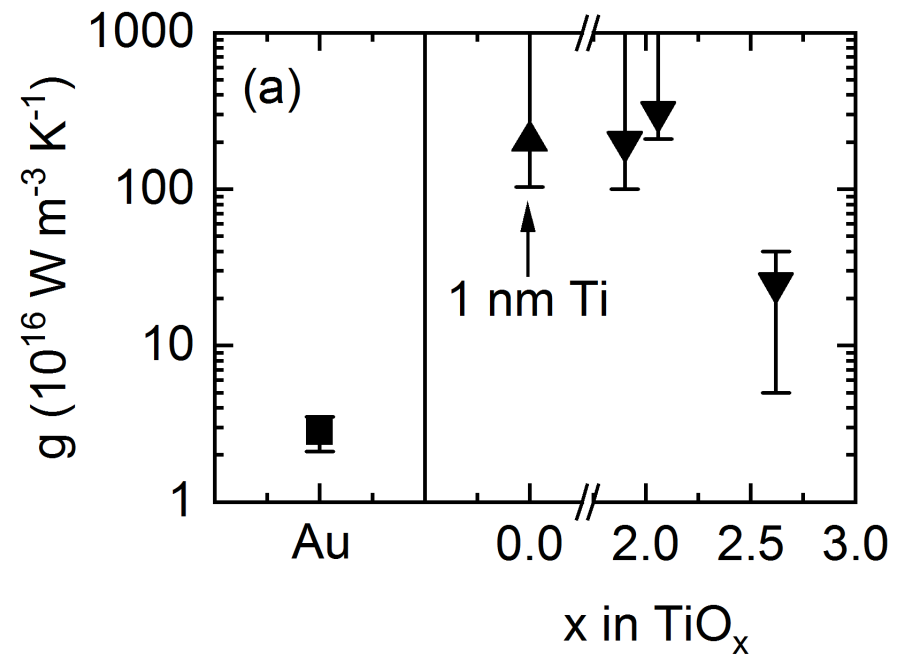
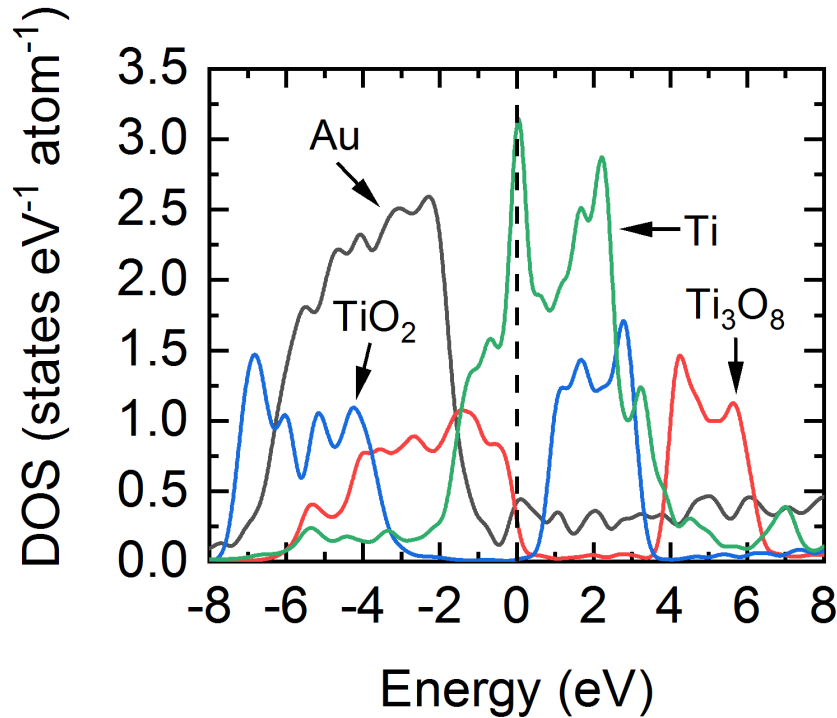


Collaboration: Khalid Hattar (SNL)



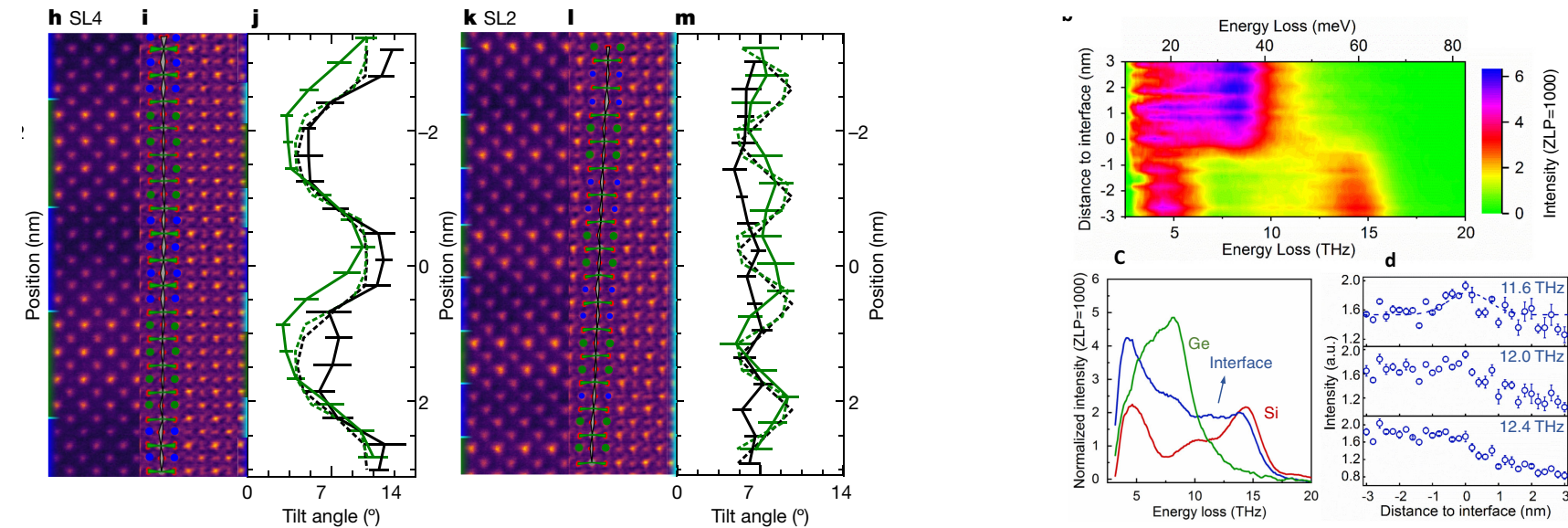
# Defects enhance electron-phonon interfacial coupling

Coupled electron-phonon thermal resistance can be impacted by chemistry at interfaces based on defect vibrational energies



# Technical challenge: spectrally resolve the existence of these unique phononic states at polar WBC and UWBG interfaces

STEM EELS offers unprecedented spatial and energy resolution to resolve these unique modes



**556** | Nature | Vol 601 | 27 January 2022 **NATURE COMMUNICATIONS** | (2021)12:6901 |

## Article

# Emergent interface vibrational structure of oxide superlattices

<https://doi.org/10.1038/s41586-021-04238-z>

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Eric R. Hoglund<sup>1,2,3</sup>, De-Liang Bao<sup>2</sup>, Andrew O'Hara<sup>2</sup>, Sara Makarem<sup>1</sup>, Zachary T. Piontkowski<sup>3</sup>, Joseph R. Matson<sup>4</sup>, Ajay K. Yadav<sup>5</sup>, Ryan C. Haislmaier<sup>6</sup>, Roman Engel-Herbert<sup>7,8</sup>, Jon F. Ihlefeld<sup>1</sup>, Jayakanth Ravichandran<sup>9</sup>, Ramamoorthy Ramesh<sup>5</sup>, Joshua D. Caldwell<sup>4</sup>, Thomas E. Beechem<sup>3,10,11</sup>, John A. Tomko<sup>12</sup>, Jordan A. Hachtel<sup>13,14</sup>, Sokrates T. Pantelides<sup>2,14,15</sup>, Patrick E. Hopkins<sup>1,2,15</sup> & James M. Howe<sup>1,3</sup>

<https://doi.org/10.1038/s41467-021-27250-3>

OPEN

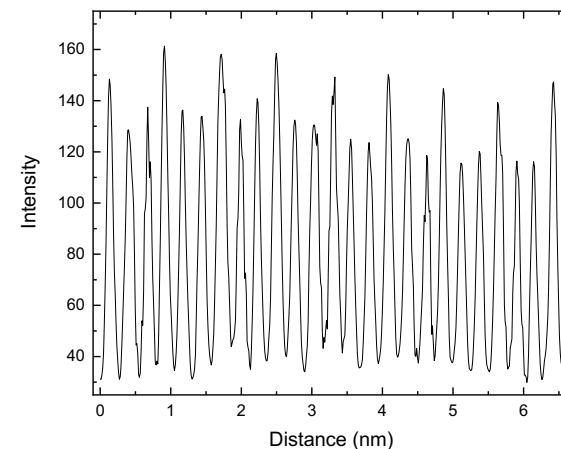
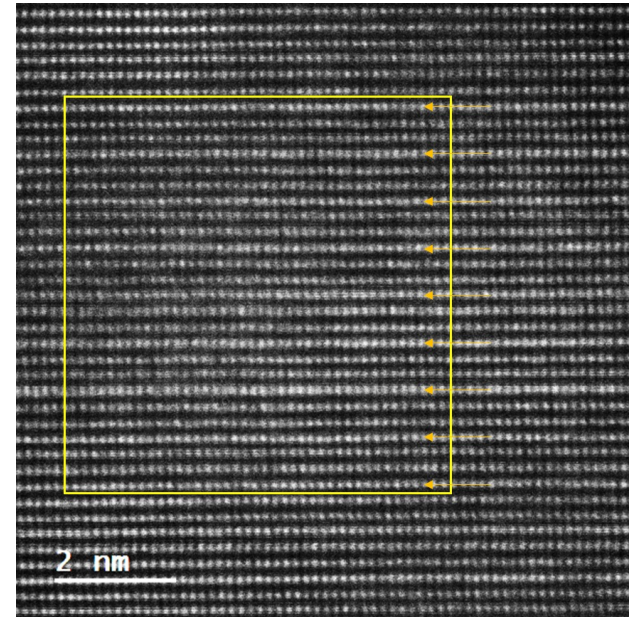
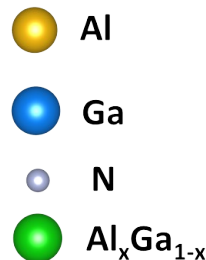
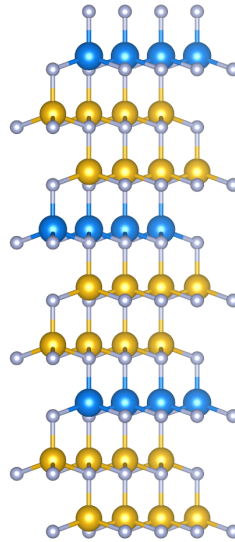
## Experimental observation of localized interfacial phonon modes

Zhe Cheng<sup>1,10,11</sup>, Ruiyang Li<sup>2,11</sup>, Xingxu Yan<sup>1,3,4,11</sup>, Glenn Jernigan<sup>5</sup>, Jingjing Shi<sup>1</sup>, Michael E. Liao<sup>6</sup>, Nicholas J. Hines<sup>1</sup>, Chaitanya A. Gadre<sup>7</sup>, Juan Carlos Idrobo<sup>8</sup>, Eungkyu Lee<sup>9</sup>, Karl D. Hobart<sup>5</sup>, Mark S. Goorsky<sup>6</sup>, Xiaoping Pan<sup>1,3,4,7</sup>, Tengfei Luo<sup>1,2</sup> & Samuel Graham<sup>1,2</sup>

# Technical challenge: Engineering WBG and UWBG materials to enhance the contribution to these modes

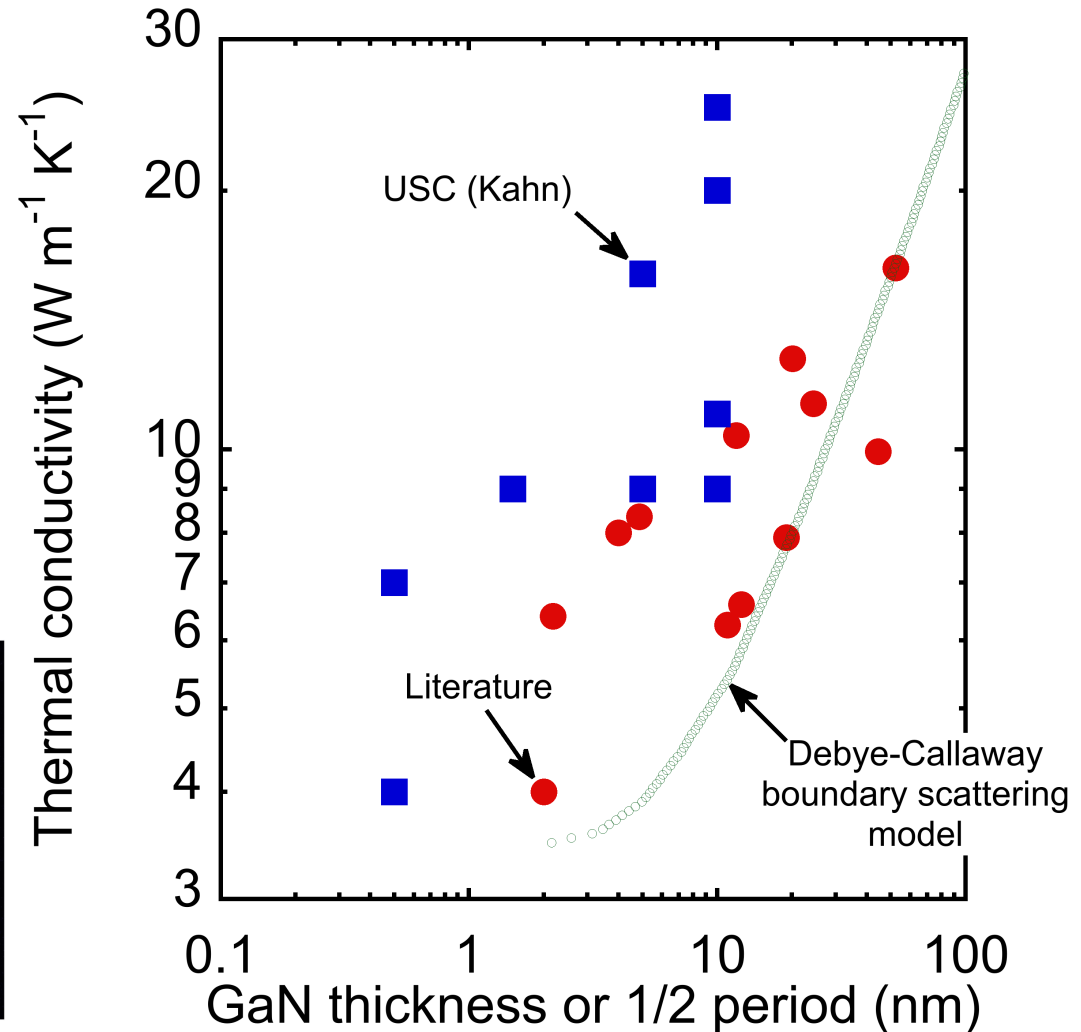
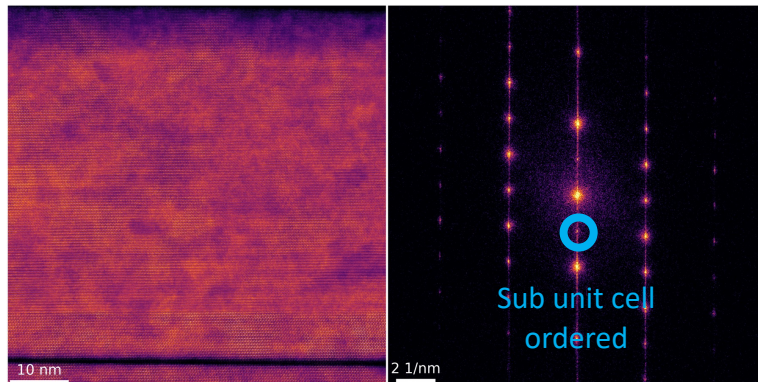
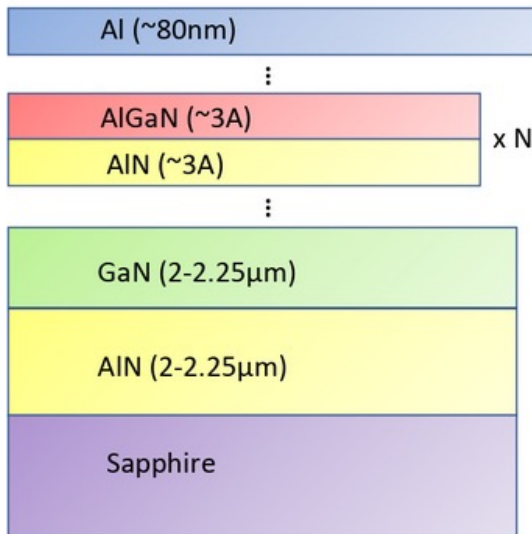
The “digital alloy” – can we chemically order “defects”?

- Digital alloys of varying periodicity grown by **Khan** and measured by **Goorsky**
- Thickness varying from a few nanometers to ~200 nm



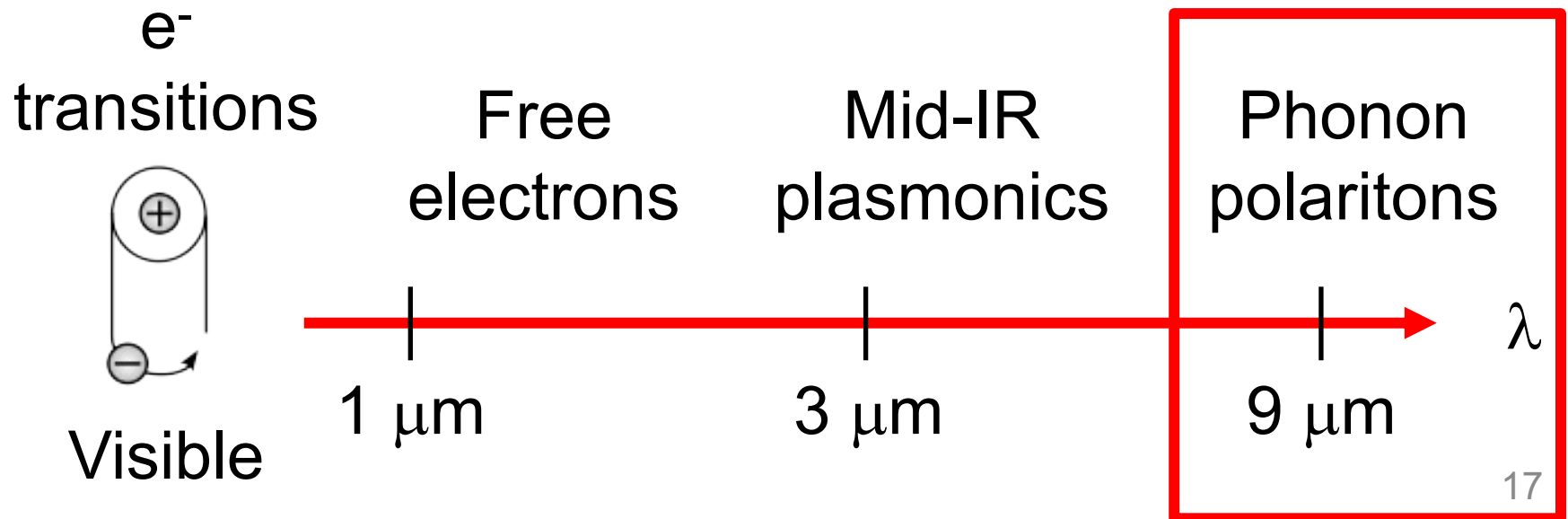
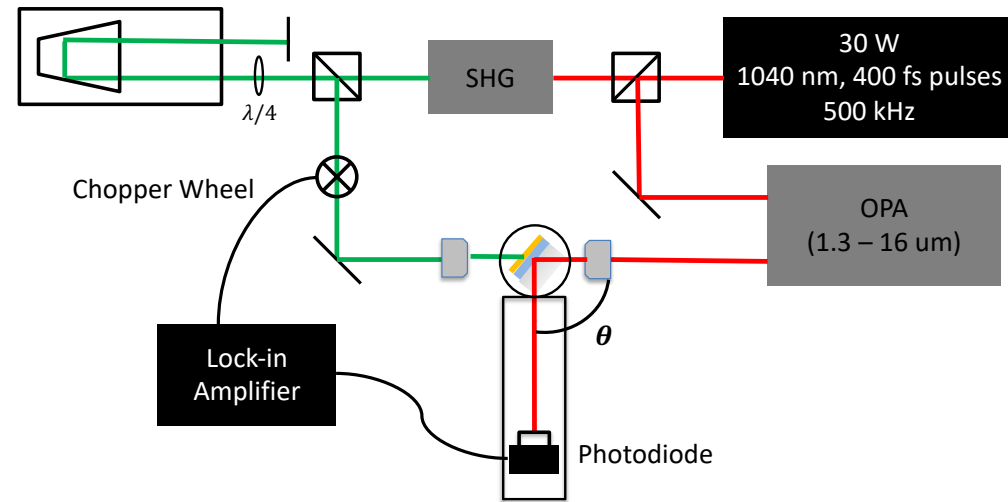
# Technical challenge: Engineering WBG and UWBG materials to enhance the contribution to these modes

## High quality SLs and the “digital alloy”

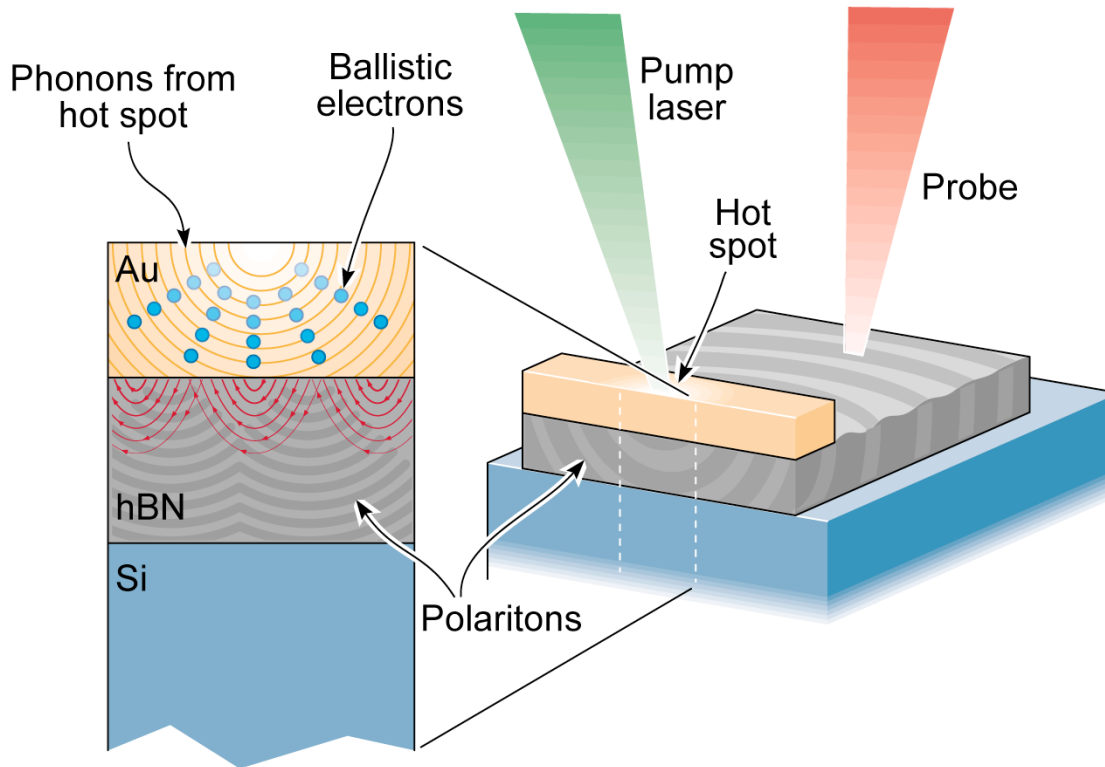


# Technical challenge: spectrally resolve the contribution of these modes to thermal transport

Can we measure the contribution to thermal conductivity from individual phonon modes?



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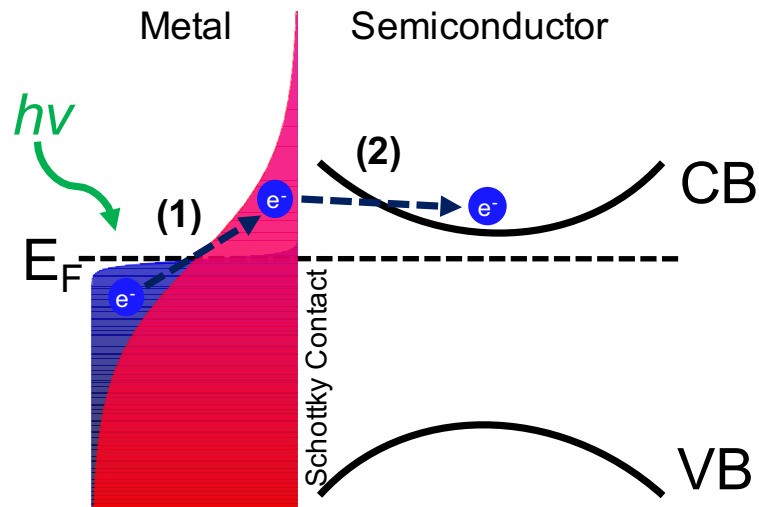
Collaboration under ARO funding  
Caldwell (Vanderbilt), Maria (PSU)



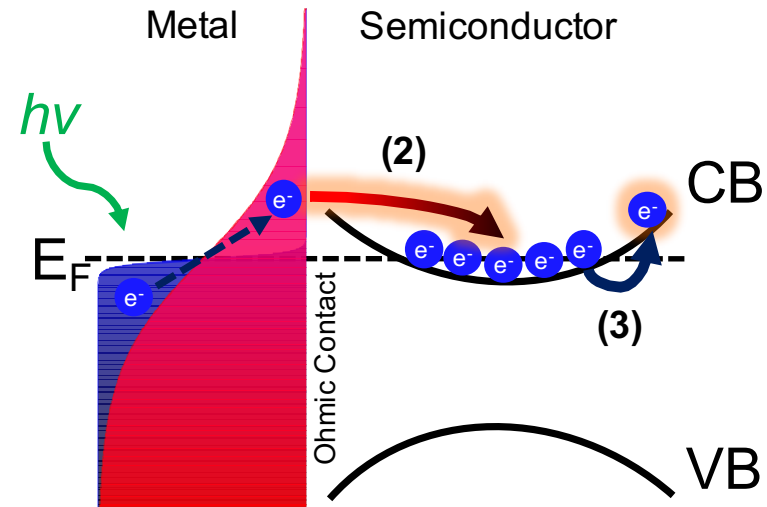
# Technical challenge: Move beyond phonon engineering and enhance TBC with electronic mechanisms

Recall: electron-electron TBC is ultrahigh compared to phonon-phonon TBC: how can we embrace this for UWBG material cooling?

a) Hot electron injection  
(Charge transfer)



b) Ballistic thermal injection  
(Energy transfer)



Tomko *et al.* *Nature Nano.* **16**, 47

Collaboration under ARO funding

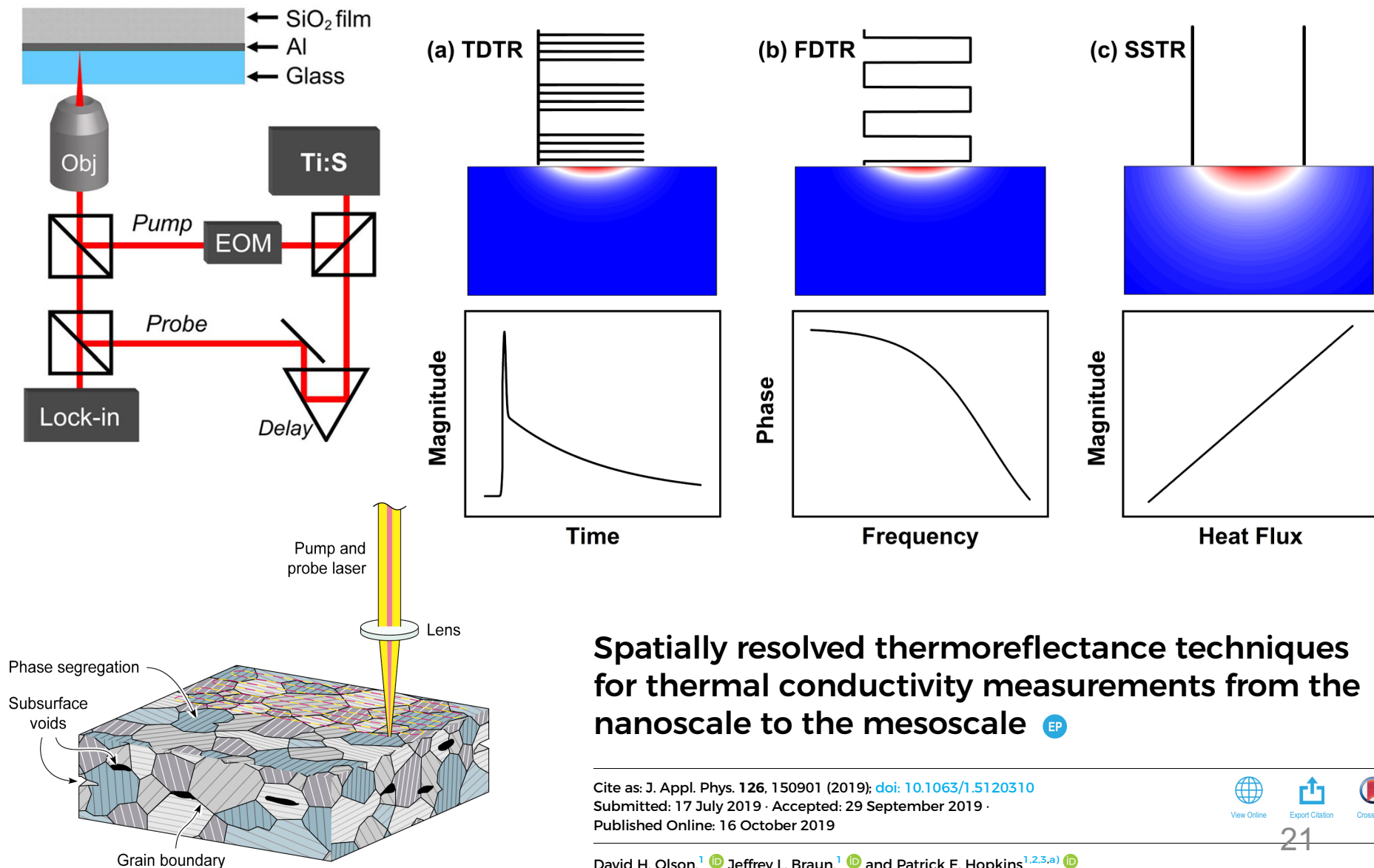
Caldwell (Vanderbilt), Maria (PSU), Prezhdov (USC)

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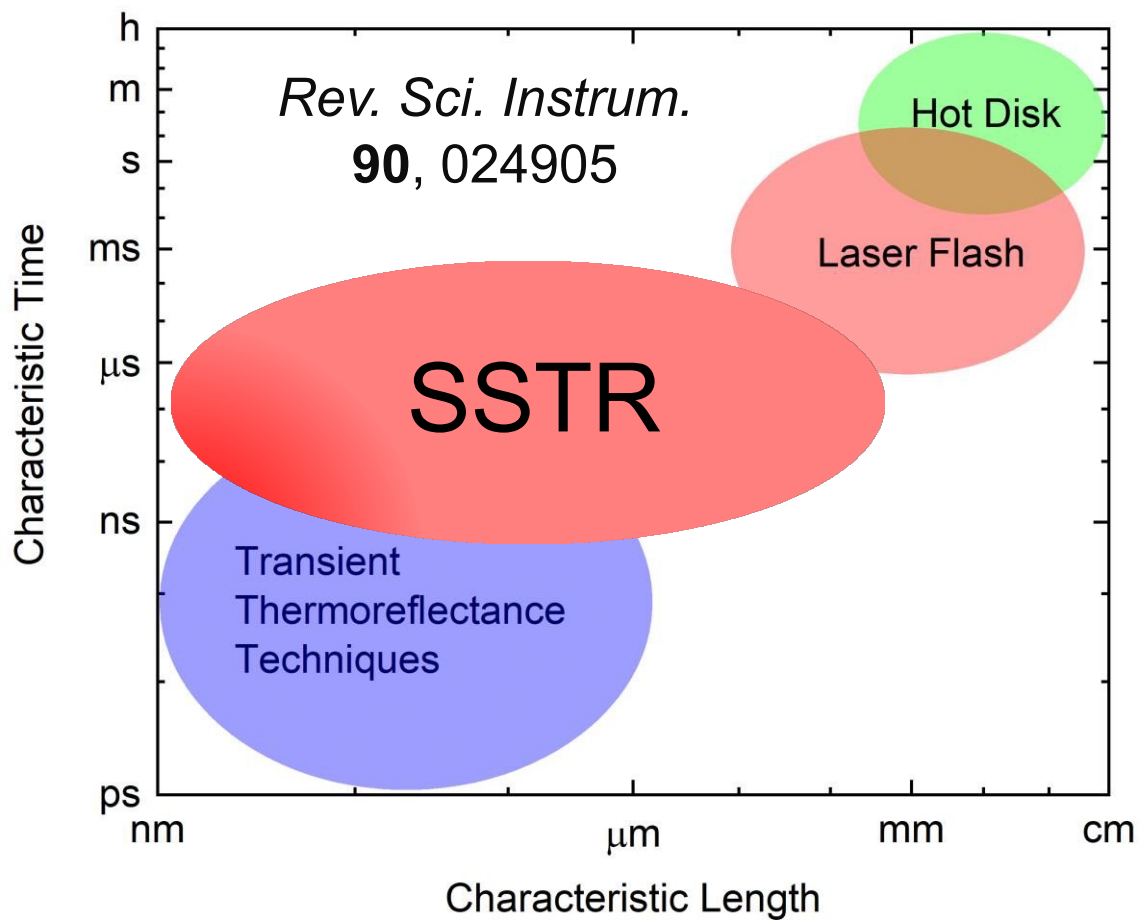
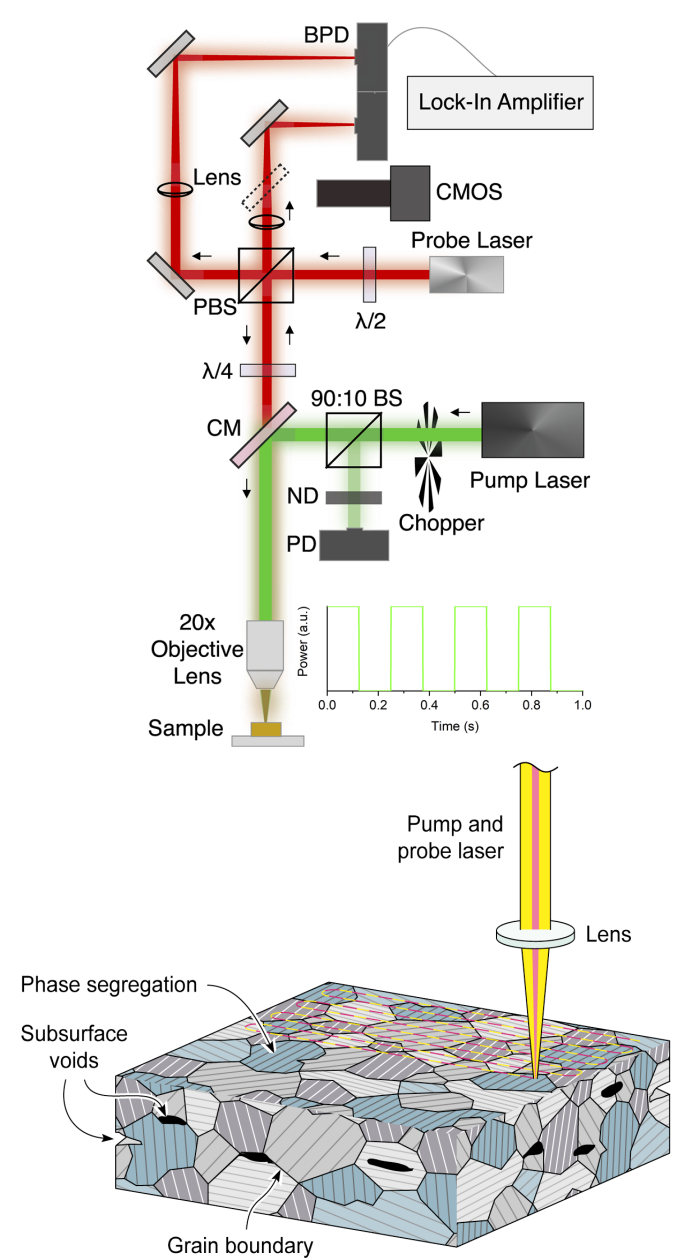
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# But how do we measure nano to macro HX processes?



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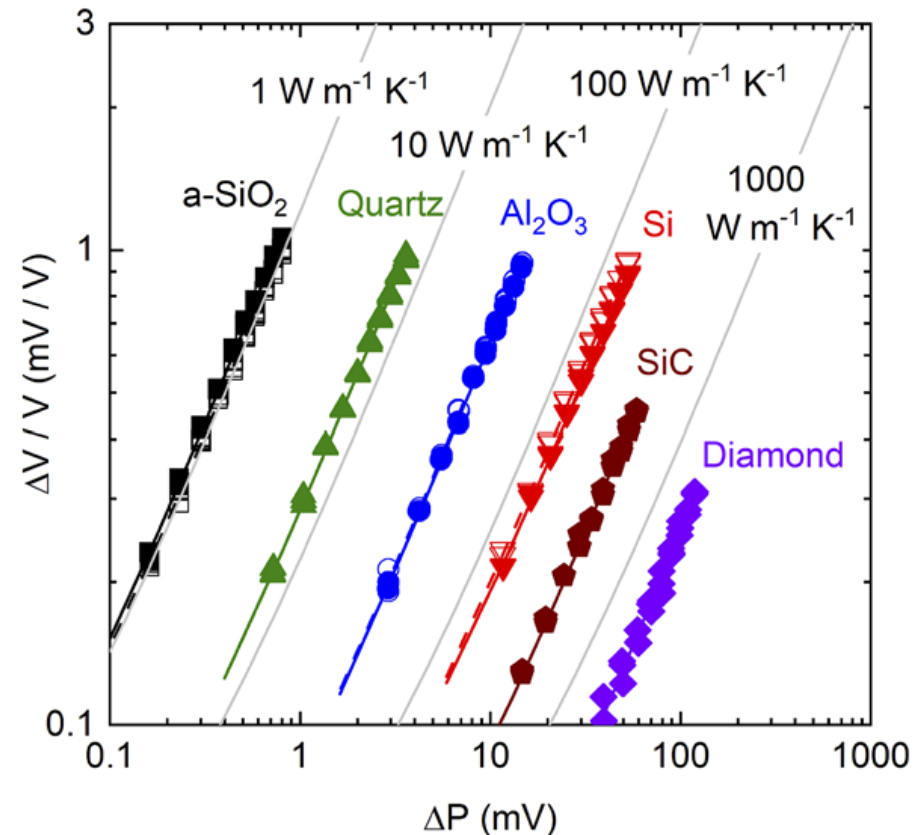
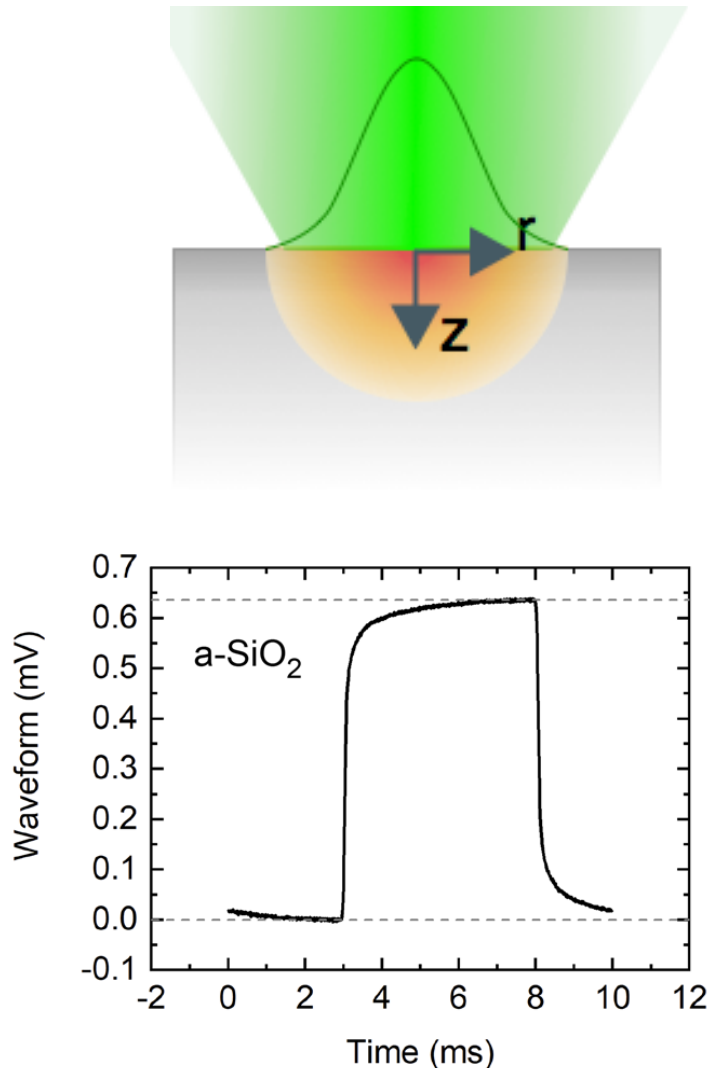
## Spatially resolved thermoreflectance techniques for thermal conductivity measurements from the nanoscale to the mesoscale EP

Cite as: J. Appl. Phys. **126**, 150901 (2019); doi: [10.1063/1.5120310](https://doi.org/10.1063/1.5120310)  
Submitted: 17 July 2019 · Accepted: 29 September 2019 ·  
Published Online: 16 October 2019

# Steady-state thermoreflectance (SSTR): How does it work?

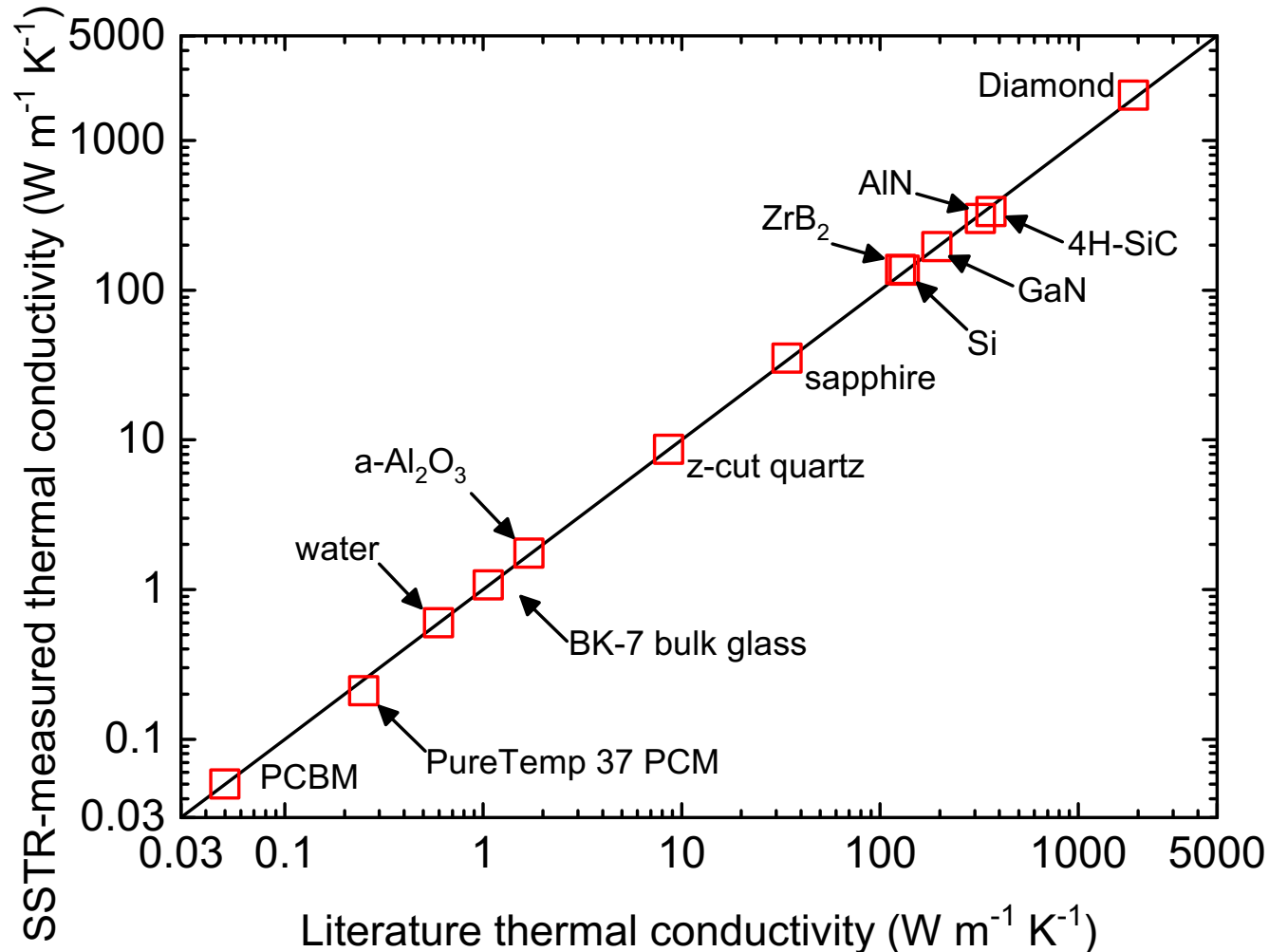
$$Q = -k \nabla T$$

Fourier's Law



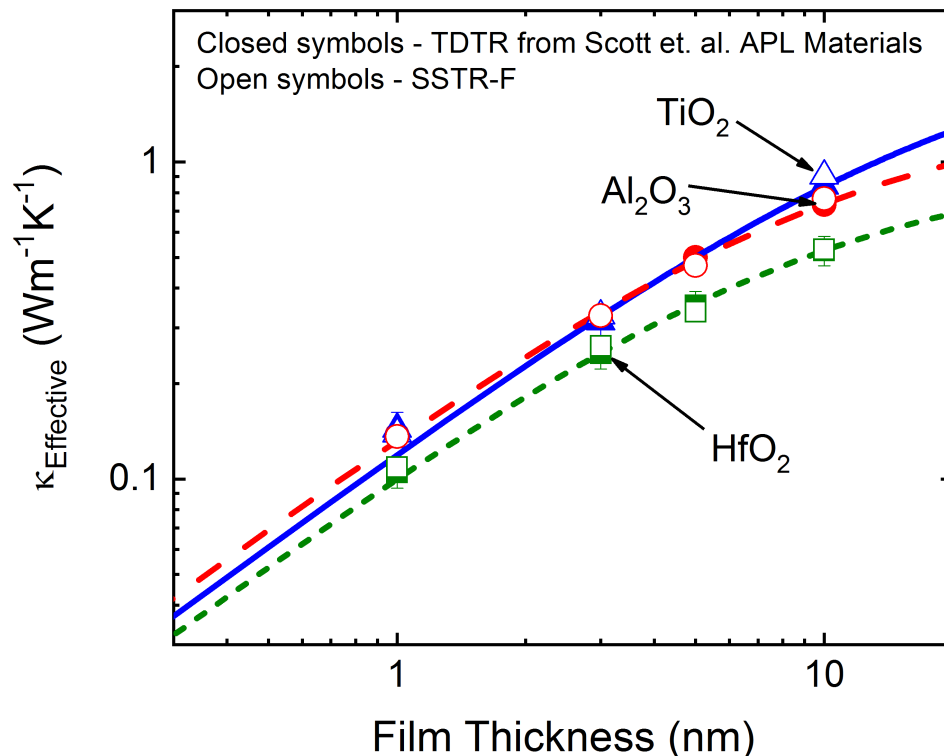
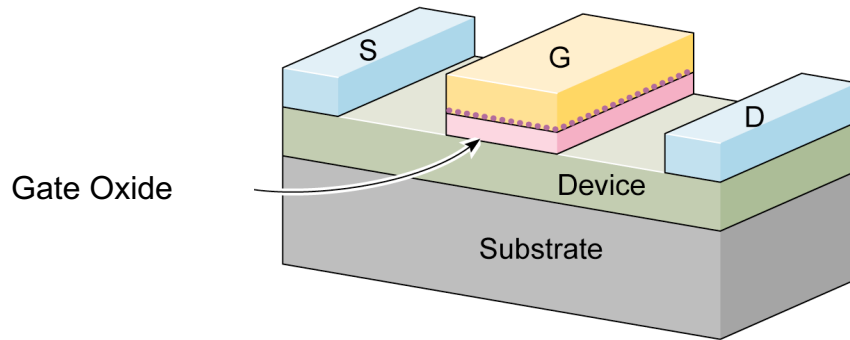
# SSTR: Capabilities for thermal conductivity measurements

Extremely conductive (diamond) and insulative (PCBM) materials



# SSTR: Capabilities for thermal conductivity measurements

## Thermal conductivity of dielectric films as thin as 1 nm

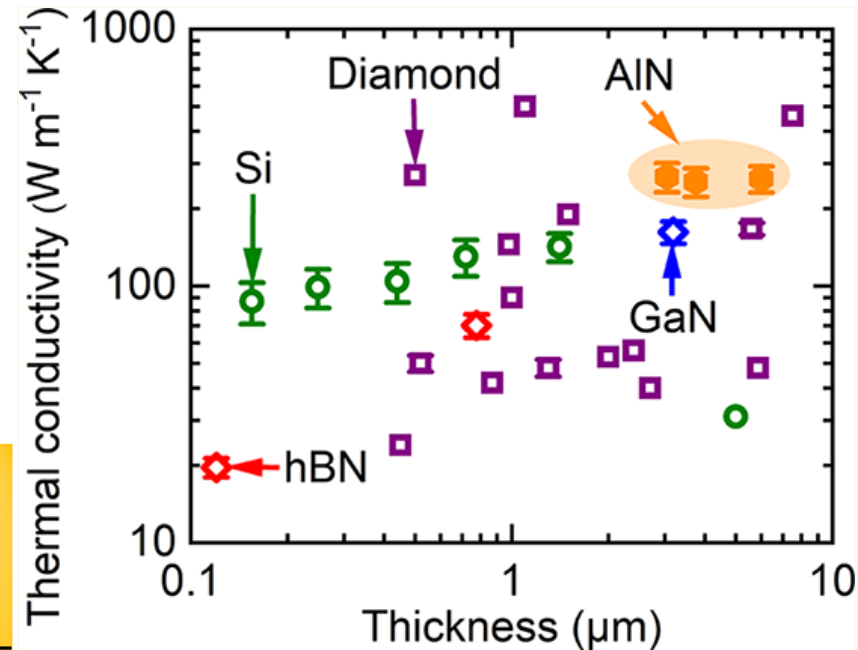
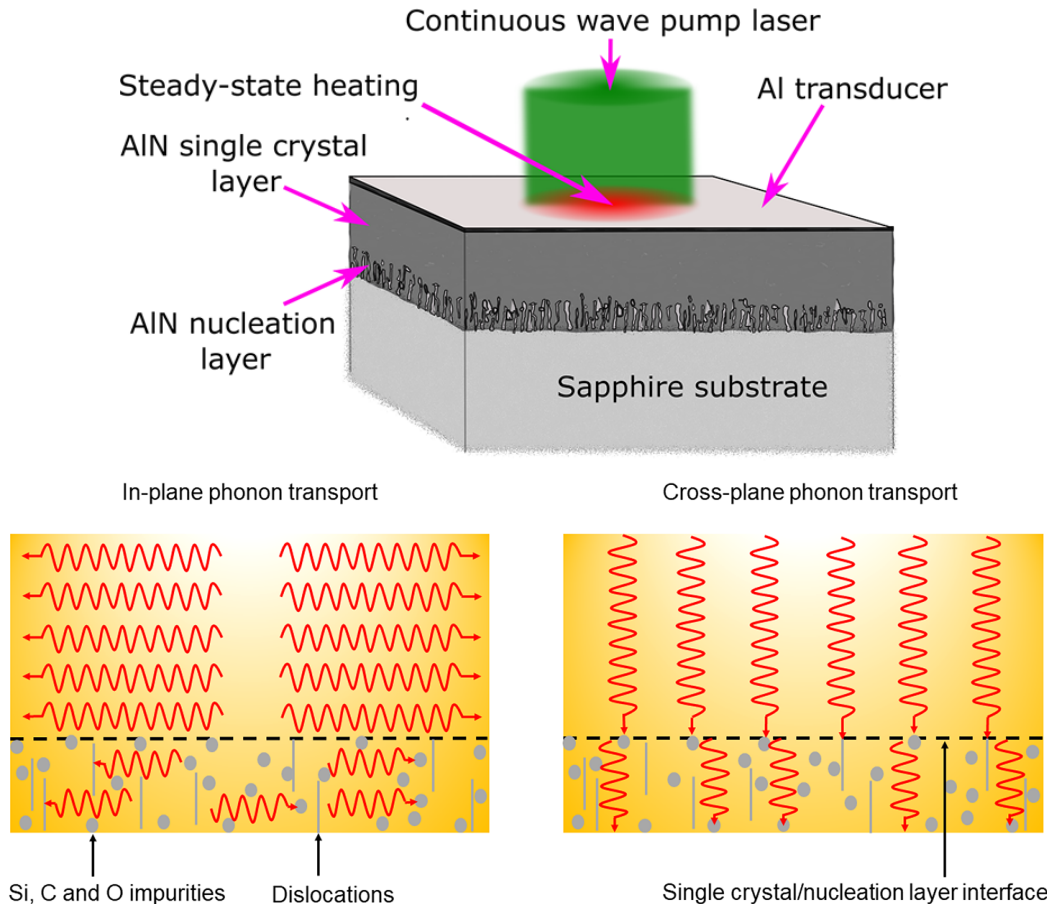


- Verified over three materials systems using SSTR-F
- Matches existing TDTR measurements
- Measuring resistance from interfaces and from material resistance in this case

*APL Materials* **6**, 058302 (2018)

# SSTR: Capabilities for thermal conductivity measurements

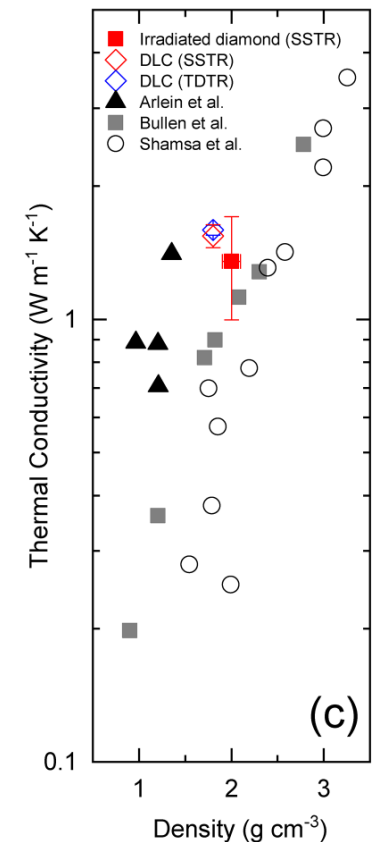
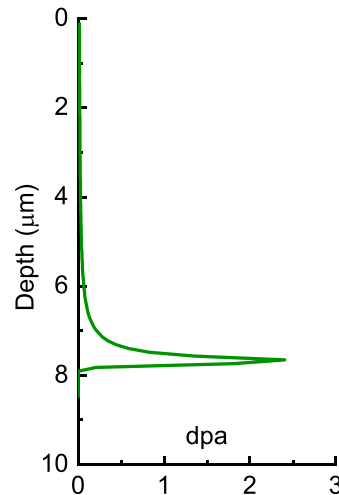
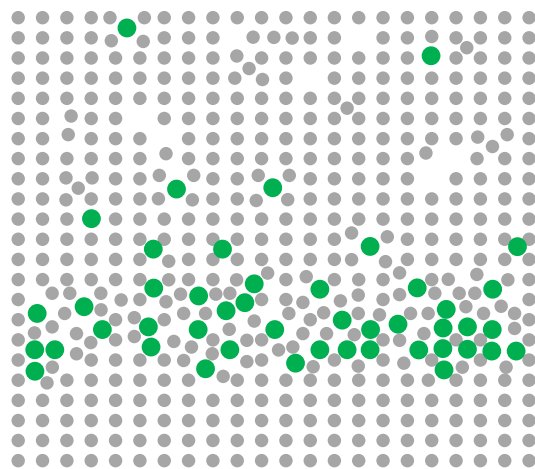
## In-plane thermal conductivity of thin films i.e., anisotropy effects in AlN thin films



# SSTR: Capabilities for thermal conductivity measurements

## Sub-surface defect detection

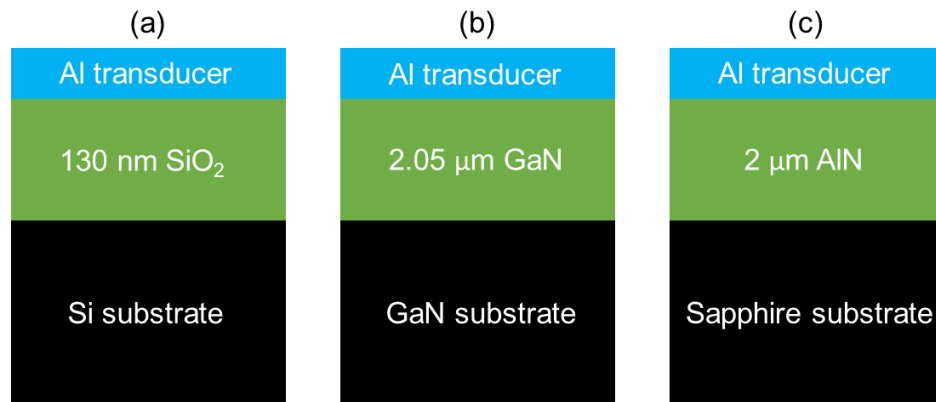
(e.g., measure thermal conductivity of thin region with point defects 7  $\mu\text{m}$  under diamond surface)



# SSTR: Capabilities for thermal conductivity measurements

## Sub-surface interfaces and heat sinks

e.g., measure thermal conductivity of buried interfaces, sub-mounts & substrates under GaN and AlN thin films



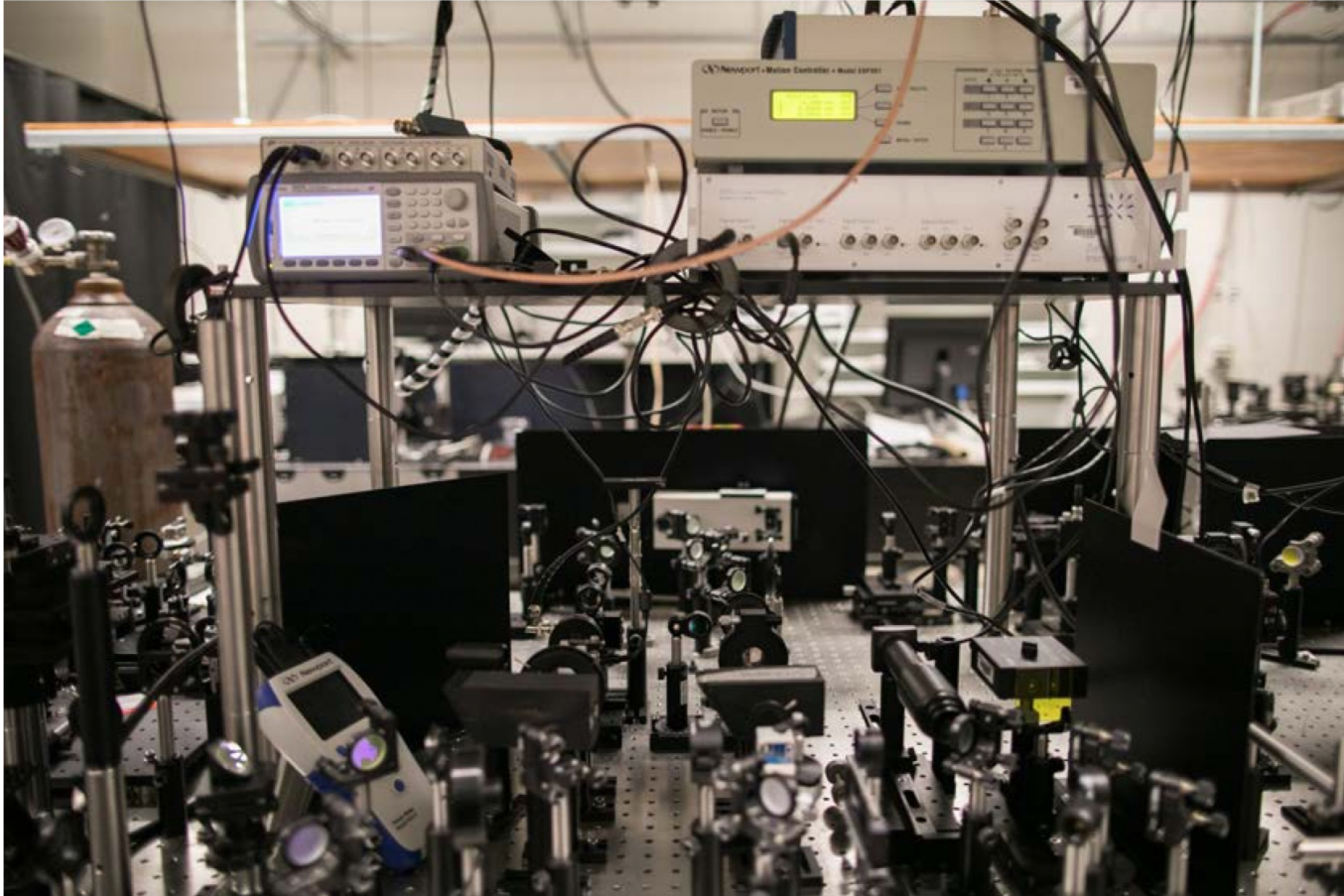
- Automated variable spot size in SSTR-F allow for control over sample depth
- Measurement of layer-by-layer thermal conductivity in electronic device stack

Substrates	Thermal conductivity (W m <sup>-1</sup> K <sup>-1</sup> )		
	spot size 10 μm	spot size 20 μm	literature
Si	141 ± 27	140 ± 18	140 <sup>30</sup>
GaN	194 ± 27	185 ± 16	195 <sup>41</sup>
Sapphire	35.1 ± 5.9	34.5 ± 4.2	35 <sup>42</sup>



# SSTR-F: Recently commercialized for turn-key, fiber-optically integrated thermal conductivity microscope

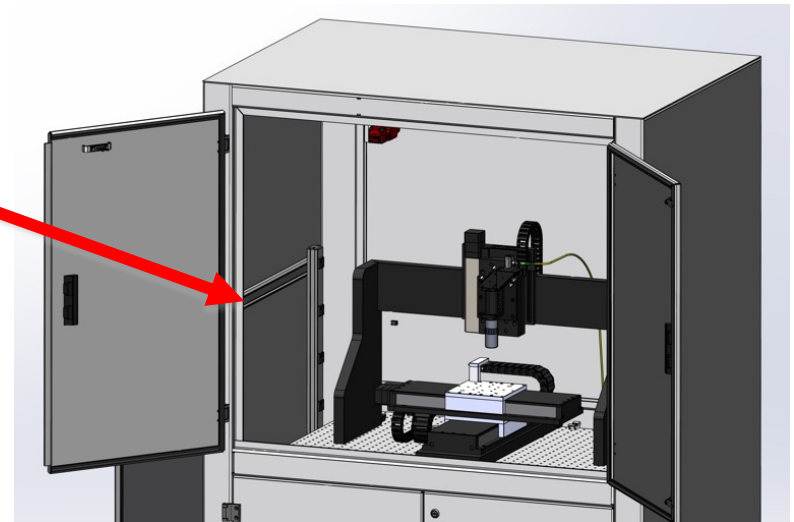
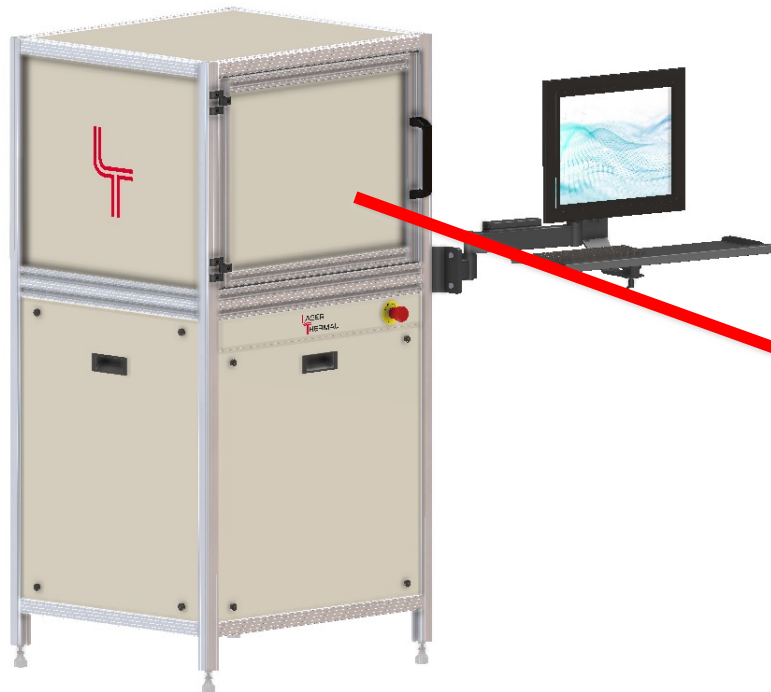
The typical thermoreflectance set up



A LOT of optics, upkeep and expertise for analysis

# SSTR-F: Commercialized for turn-key thermal conductivity microscope for bulk materials, thin films and interfaces

<https://Laserthermal.com>



**FULL DISCLOSURE: HOPKINS IS A  
CO-FOUNDER OF THIS COMPANY**

# Summary and key challenges

- **Key Take Away #1:** Defects and interfaces can be developed to enhance electron and phonon thermal transport
  - *Challenge:* Growth of thin films with controlled spatial arrangements of defects and interfaces
  - *Challenge:* Harness coupled carriers (e.g., electron-phonon, polaritons) to bypass large phonon transport and directionally control thermal transport
- **Key Take Away #2:** New metrologies can measure spatial, temporal and spectral contribution of electron and phonon transport
  - *Challenge:* Measure and manipulate interfacial modes to enhance thermal transport
  - *Challenge:* Measure and manipulate coupled carrier's contribution to thermal transport across interface
  - *Challenge:* Translate thermal metrologies to materials and device labs and industry

